

LINEAR SYSTEMS

Linear Integrated Systems

FEATURES

Direct Replacement For SILICONIX 2N/SST4416 & 2N4416A

VERY LOW NOISE FIGURE (400 MHz)	4 dB (max)
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EXCEPTIONAL GAIN (400 MHz)	10 dB (min)
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ABSOLUTE MAXIMUM RATINGS¹

@ 25 °C (unless otherwise stated)

Maximum Temperatures

Storage Temperature	-65 to +200 °C
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Operating Junction Temperature	-55 to +135 °C
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Maximum Power Dissipation

Continuous Power Dissipation	300mW
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Maximum Currents

Gate Current	10mA
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Maximum Voltages

Gate to Drain or Gate to Source LS4416	-30V
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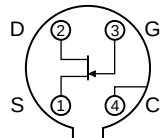
Gate to Drain or Gate to Source LS4416A	-35V
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2N/SST4416 2N4416A

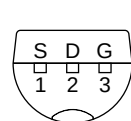
N-CHANNEL JFET HIGH FREQUENCY AMPLIFIER

2N SERIES 2N SERIES* SST SERIES

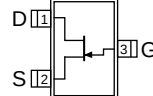
TO-72
BOTTOM VIEW



TO-92
BOTTOM VIEW



SOT-23
TOP VIEW



*Optional Package For 2N4416

ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
BV _{GSS}	Gate to Source Breakdown Voltage	2N/SST4416	-30		V	I _G = -1μA, V _{DS} = 0V
		2N4416A	-35			
V _{GS(off)}	Gate to Source Cutoff Voltage	2N/SST4416		-6		V _{DS} = 15V, I _D = 1nA
		2N4416A	-2.5	-6		
I _{DSS}	Gate to Source Saturation Current	5		15	mA	V _{DS} = 15V, V _{GS} = 0V
I _{GSS}	Gate Leakage Current	2N		-0.1	nA	V _{GS} = -20V, V _{DS} = 0V
		SST		-1.0		V _{GS} = -15V, V _{DS} = 0V
g _{fs}	Forward Transconductance	4500		7500	μS	V _{DS} = 15V, V _{GS} = 0V, f = 1kHz
g _{os}	Output Conductance			50		
C _{iss}	Input Capacitance ²			0.8	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
C _{rss}	Reverse Transfer Capacitance ²			4		
C _{oss}	Output Capacitance ²			2		
e _n	Equivalent Input Noise Voltage		6		nV/√Hz	V _{DS} = 10V, V _{GS} = 0V, f = 1kHz

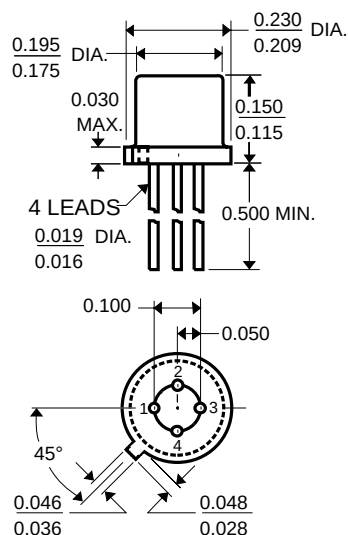
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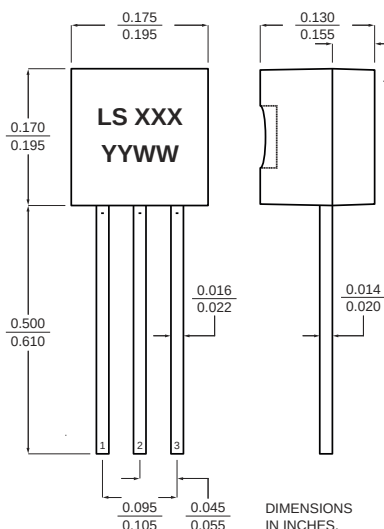
HIGH FREQUENCY ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	100 MHz		400 MHz		UNITS	CONDITIONS
		MIN	MAX	MIN	MAX		
g_{iss}	Input Conductance		100		1000	μS	$V_{DS} = 15V, V_{GS} = 0V$
b_{iss}	Input Susceptance ²		2500		10000		
g_{oss}	Output Conductance		75		100		
b_{oss}	Output Susceptance ²		1000		4000		
G_{fs}	Forward Transconductance			4000		dB	$V_{DS} = 15V, I_D = 5mA$
G_{ps}	Power Gain ²	18		10			$V_{DS} = 15V, I_D = 5mA, R_G = 1k\Omega$
NF	Noise Figure ²		2		4		

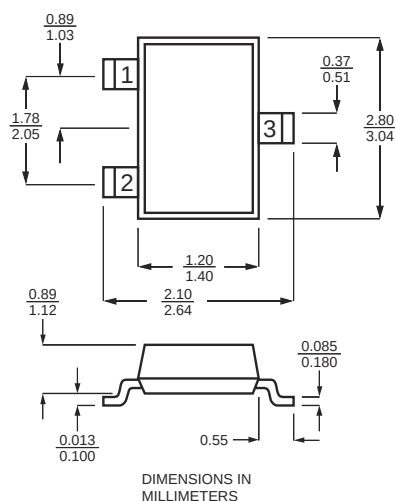
TO-72 Four Lead



TO-92



SOT-23



1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Not production tested, guaranteed by design.

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